NSN 5961-01-367-1966

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-367-1966 **Inclosure Material:** Metal **Overall Length:** Between 0.010 inches and 0.020 inches **Overall Height:** Between 0.005 inches and 0.010 inches **Mounting Facility Quantity: Mounting Method:** Threaded hole **Features Provided:** Burn in and gold plated leads **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, instantaneous **Current Rating Per Characteristic:** 10.00 microamperes collector current, dc peak **Special Features:** Nuclear hardness process; junction pattern arrangement: pn **Nuclear Hardness Critical Feature:** Hardened **Precious Material And Location:** Terminals gold **Precious Material:** Gold **Terminal Type And Quantity:** 1 unthreaded hole and 1 bonding pad Shelf Life: N/a **Unit Of Measure:**

Demilitarization: Yes - demil/mli

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